1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1 kV
- Ultra thin package profile with 0.37 mm height

3. Applications

- Relay driver
- High-speed line driver
- · High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-50	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-	-230	mA
Static charac	teristics			•			
R _{DSon}	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$		-	4.5	7.5	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



50 V, single P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D '
2	S	source	3	
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G S 017aaa259

6. Ordering information

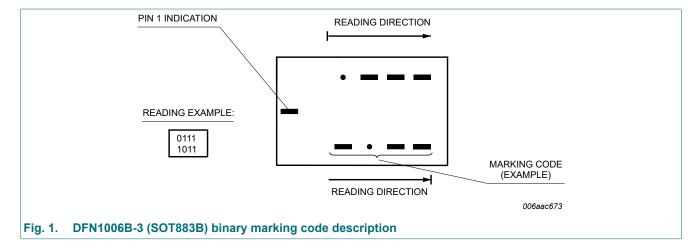
Table 3. Ordering information

Type number Package							
	Name	Description	Version				
BSS84AKMB		plastic, leadless ultra small plastic package; 3 solder lands; 0.35 mm pitch; 1.0 mm x 0.6 mm x 0.37 mm body	SOT883B				

7. Marking

Table 4. Marking codes

Type number	Marking code
BSS84AKMB	0000 0010



8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-50	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-230	mA
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-150	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-0.9	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode				•	
Is	source current	T _{amb} = 25 °C	[1]	-	-230	mA
ESD maxim	um rating		'	'		
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	1000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

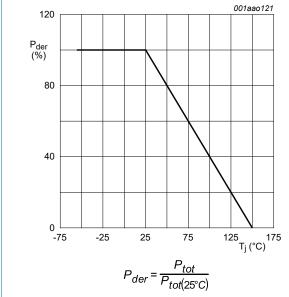


Fig. 2. Normalized total power dissipation as a function of junction temperature

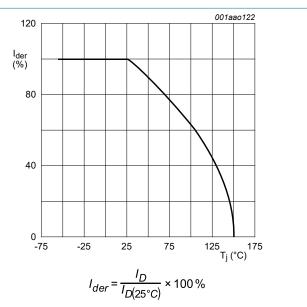


Fig. 3. Normalized continuous drain current as a function of junction temperature

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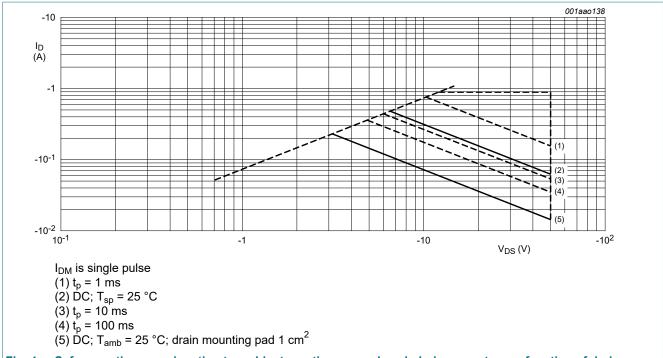


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

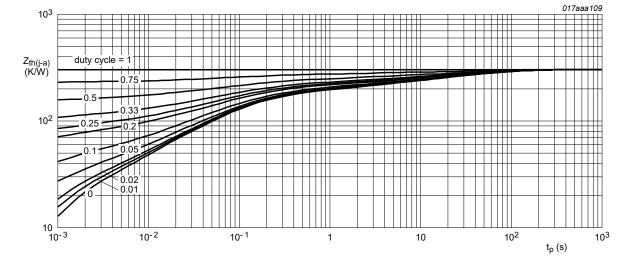
50 V, single P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

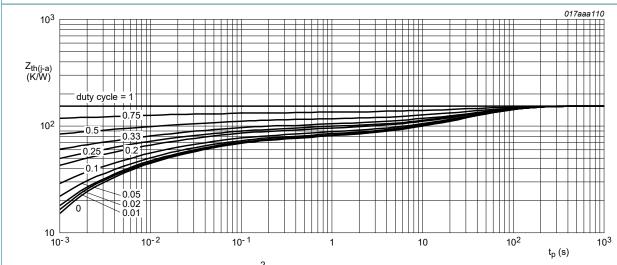
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	305	350	K/W
junction to ambient	junction to ambient		[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, single P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-50	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	V _{DS} = -50 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{DS} = -50 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-2	μΑ
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -100 mA; T_j = 25 °C	-	4.5	7.5	Ω
re	resistance	V _{GS} = -10 V; I _D = -100 mA; T _j = 150 °C	-	8	13.5	Ω
		V _{GS} = -5 V; I _D = -100 mA; T _j = 25 °C	-	5.7	8.5	Ω
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	150	-	mS
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -25 \text{ V}; I_D = -200 \text{ mA}; V_{GS} = -5 \text{ V};$	-	0.26	0.35	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge	V_{DS} = -10 V; I_{D} = -200 mA; V_{GS} = -5 V; I_{j} = 25 °C	-	0.09	-	nC
C _{iss}	input capacitance	V _{DS} = -25 V; f = 1 MHz; V _{GS} = 0 V;	-	24	36	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.5	-	pF
C _{rss}	reverse transfer capacitance		-	1.3	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -30 \text{ V}; R_L = 250 \Omega; V_{GS} = -10 \text{ V};$	-	13	26	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t _{d(off)}	turn-off delay time		-	48	96	ns
t _f	fall time]	-	25	-	ns
Source-drai	in diode		'	,	,	
V_{SD}	source-drain voltage	$I_S = -115 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-0.48	-0.85	-1.2	V

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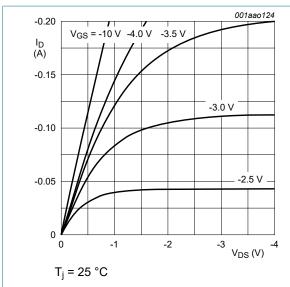
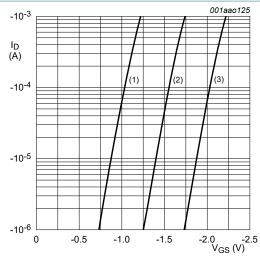


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values



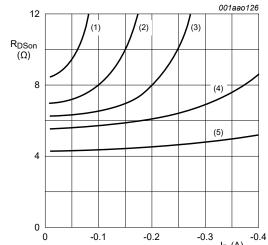
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Sub-threshold drain current as a function of Fig. 8. gate-source voltage



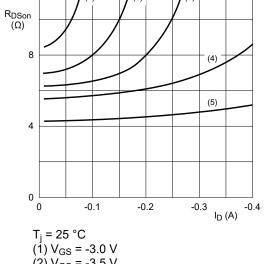
 $(2) V_{GS} = -3.5 V$

(3) $V_{GS} = -4.0 \text{ V}$

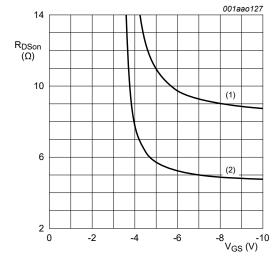
 $(4) V_{GS} = -5.0 V$

 $(5) V_{GS} = -10.0 V$ Fig. 9.

of drain current; typical values



Drain-source on-state resistance as a function



 $I_D = -200 \text{ mA}$

(1) $T_i = 150 \, ^{\circ}C$

 $(2) T_{j} = 25 ^{\circ}C$

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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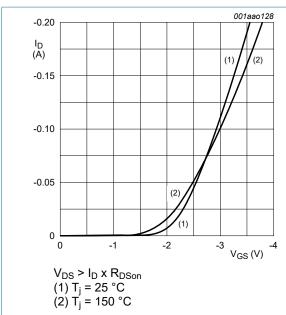


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

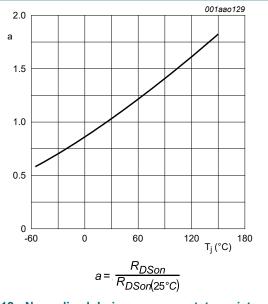
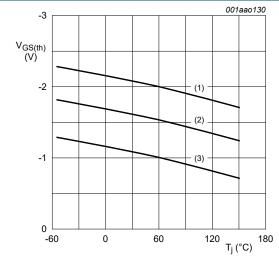


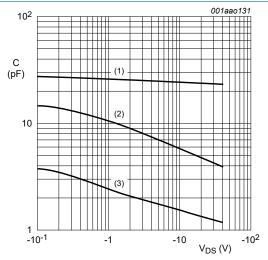
Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz, V_{GS} = 0 V$

- $(1) C_{iss}$
- (2) C_{oss}
- (3) C_{rss}

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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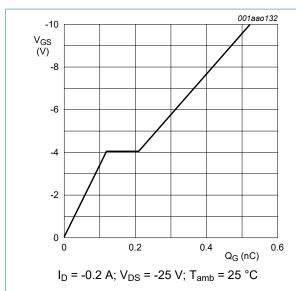


Fig. 15. Gate-source voltage as a function of gate charge; typical values

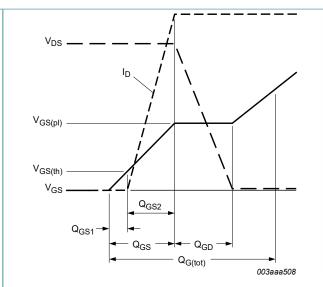
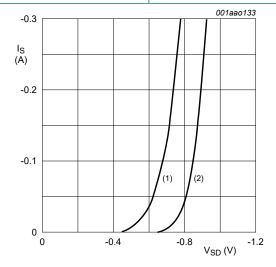


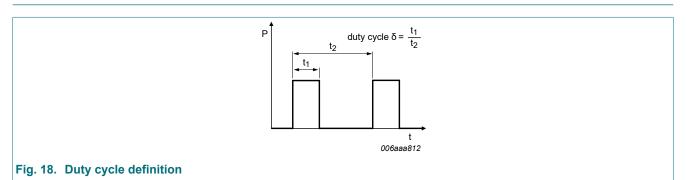
Fig. 16. Gate charge waveform definitions



 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$ (2) $T_j = 25 \,^{\circ}C$

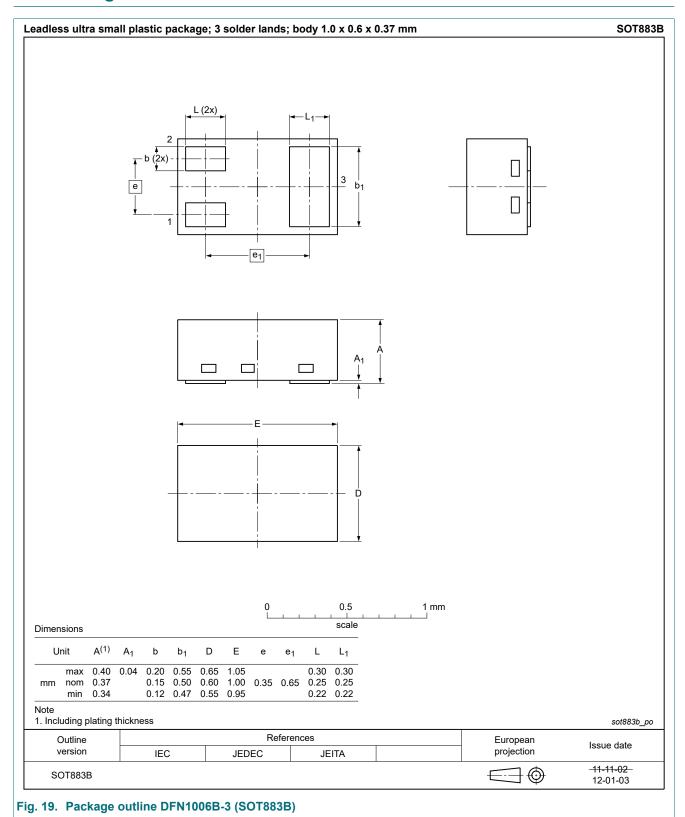
Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information



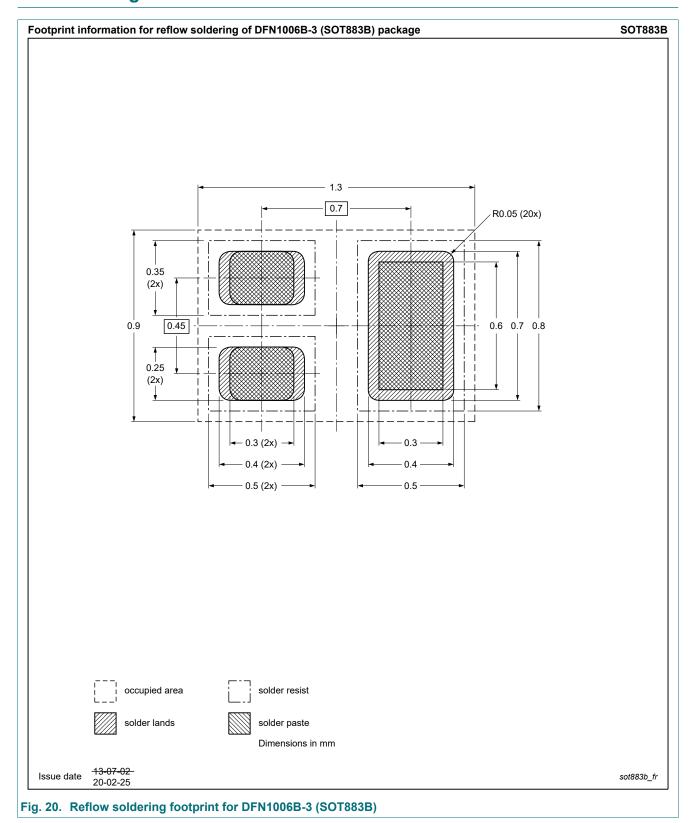
50 V, single P-channel Trench MOSFET

12. Package outline



50 V, single P-channel Trench MOSFET

13. Soldering



50 V, single P-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
BSS84AKMB v.2	20201027	Product data sheet	-	BSS84AKMB v.1				
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 							
BSS84AKMB v.1	20120606	Product data sheet	-	-				

50 V, single P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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	Features and benefits

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